

CMKD6263

**SURFACE MOUNT
TRIPLE ISOLATED
HIGH VOLTAGE SILICON
SCHOTTKY DIODES**



www.centrasemi.com

ULTRAmi™



SOT-363 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6263 contains three (3) galvanically isolated, high voltage Silicon Schottky diodes, epoxy molded in a SOT-363 surface mount package. This ULTRAmi™ device has been designed for fast switching applications requiring a low forward voltage drop.

MARKING CODE: K63

FEATURES:

- Meets Galvanic Isolation Requirements of IEEE 1394
- High Voltage (70V)
- ULTRAmi™ Package
- Requires less board space than 3 individual diodes
- Low Forward Voltage

MAXIMUM RATINGS: (T_A=25°C)

Peak Repetitive Reverse Voltage
 Continuous Forward Current
 Peak Forward Surge Current, tp=1.0s
 Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL

SYMBOL		UNITS
V _{RRM}	70	V
I _F	15	mA
I _{FSM}	50	mA
P _D	250	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

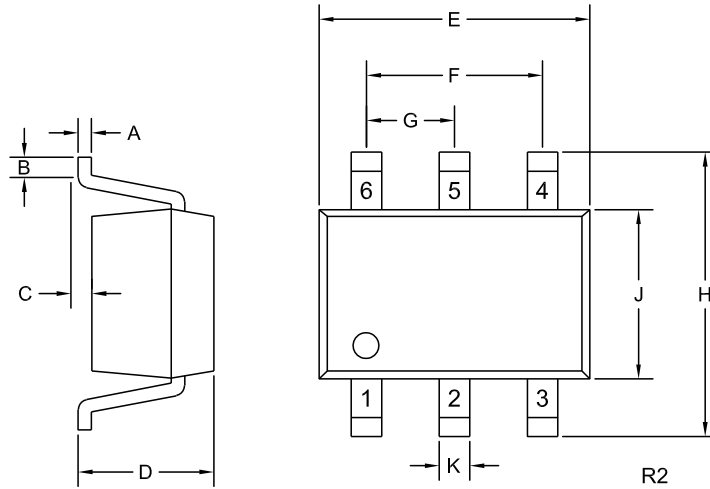
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =50V		98	200	nA
BV _R	I _R =10μA	70			V
V _F	I _F =1.0mA		395	410	mV
C _T	V _R =0, f=1.0MHz			2.0	pF
t _{rr}	I _R =I _F =10mA, I _{rr} =1.0mA, R _L =100Ω			5.0	ns

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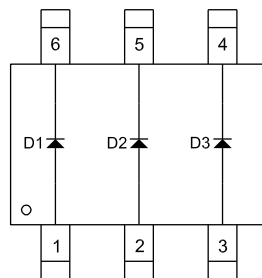
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SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

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R4 (13-January 2010)